BA282, BA283

SILICON EPITAXIAL PLANAR DIODE SWITCHES

for electronic band-switching in radio and TV tuners in the frequency range of 50 to 1000 MHz. The dynamic forward resistance is constant and very small over a wide range of frequency and forward current. The reverse capacitance is also small and largely independent of the reverse voltage.

These diodes are delivered taped.
Details see “Taping”.

Absolute Maximum Ratings (T_a = 25°C)

<table>
<thead>
<tr>
<th>Symbol</th>
<th>Value</th>
<th>Unit</th>
</tr>
</thead>
<tbody>
<tr>
<td>V_R</td>
<td>35</td>
<td>V</td>
</tr>
<tr>
<td>I_F</td>
<td>100</td>
<td>mA</td>
</tr>
<tr>
<td>T_j</td>
<td>150</td>
<td>°C</td>
</tr>
<tr>
<td>T_S</td>
<td>-55 to +150</td>
<td>°C</td>
</tr>
</tbody>
</table>

Characteristics at T_j = 25°C

<table>
<thead>
<tr>
<th>Symbol</th>
<th>Min.</th>
<th>Typ.</th>
<th>Max.</th>
<th>Unit</th>
</tr>
</thead>
<tbody>
<tr>
<td>V_F</td>
<td>-</td>
<td>-</td>
<td>1</td>
<td>V</td>
</tr>
<tr>
<td>I_R</td>
<td>-</td>
<td>-</td>
<td>50</td>
<td>nA</td>
</tr>
<tr>
<td>r_f</td>
<td>-</td>
<td>-</td>
<td>0.7</td>
<td>Ω</td>
</tr>
<tr>
<td>r_f</td>
<td>-</td>
<td>-</td>
<td>1.2</td>
<td>Ω</td>
</tr>
<tr>
<td>r_f</td>
<td>-</td>
<td>-</td>
<td>0.5</td>
<td>Ω</td>
</tr>
<tr>
<td>r_f</td>
<td>-</td>
<td>-</td>
<td>0.9</td>
<td>Ω</td>
</tr>
<tr>
<td>C_tot</td>
<td>-</td>
<td>-</td>
<td>1.5</td>
<td>pF</td>
</tr>
<tr>
<td>C_tot</td>
<td>-</td>
<td>-</td>
<td>1.25</td>
<td>pF</td>
</tr>
<tr>
<td>L_S</td>
<td>-</td>
<td>2.5</td>
<td>-</td>
<td>nH</td>
</tr>
</tbody>
</table>
Capacitance versus reverse voltage

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Capacitance versus reverse voltage

Dynamic forward resistance versus forward current

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Dynamic forward resistance versus forward current

Tj=25°C
f=1MHz

Ctot

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Tamb=25°C

rf

IF

BA283

BA283

100MHz

BA283

100MHz

BA283

100MHz

BA282

100MHz

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